
Poster Presentation

[AMDp1]Oxide TFTs

Thu. Nov 28, 2019 10:40 AM - 1:10 PM Main Hall (1F)

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[AMDp1-13]High-Mobility and High-Reliability Top-Gate Self-Aligned IGZO TFTs with incorporate high density passivation layer (HDP) after PV deposition

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Keywords:Top gate self-align IGZO TFT, high density passivation layer(HDP), high reliability

A top-gate self-aligned IGZO TFT with HDP incorporation after PV deposition was developed. The addition of HDP can effectively hamper the invasion of the outside water and gas, reduce the defects of the IGZO interface and subgap. Finally, high-mobility and high-reliability self-aligned IGZO TFT with PBTS 1.57V and NBTiS 1.03V was obtained.